

●Application

Low current rectification

●Features

1) Ultra small mold type.
(UMD4)

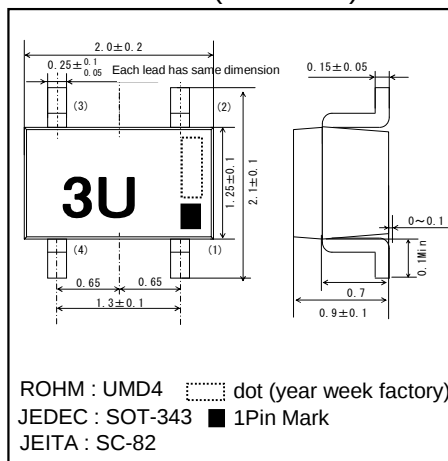
2) Low V_F

3) High reliability

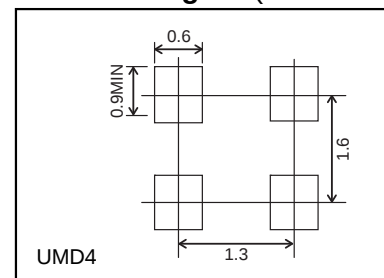
●Construction

Silicon epitaxial planar

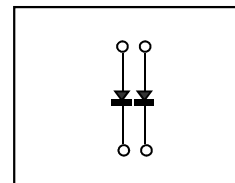
●Dimensions (Unit : mm)



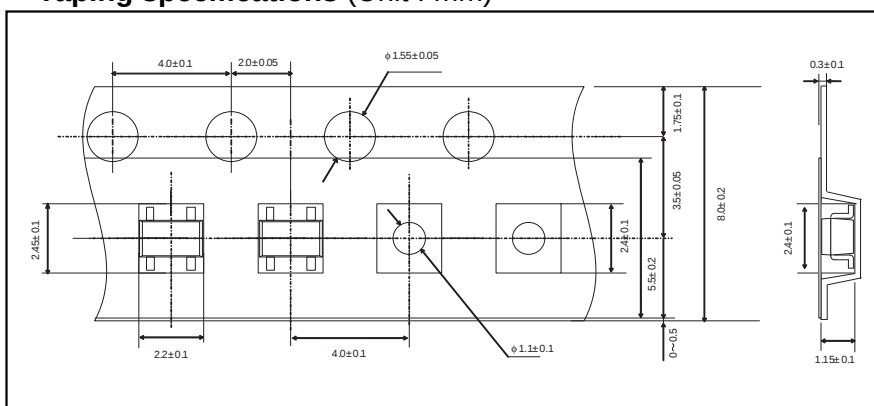
●Land size figure (Unit : mm)



●Structure



●Taping specifications (Unit : mm)



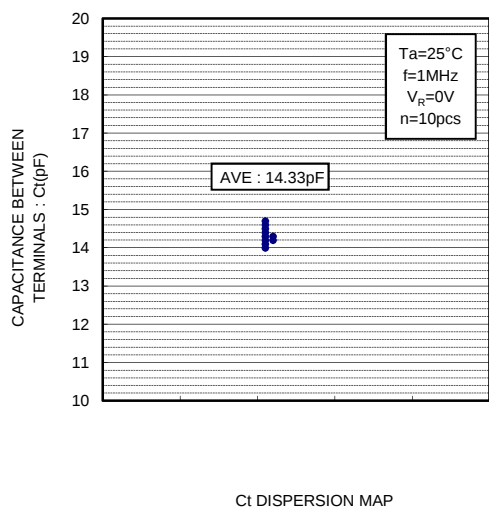
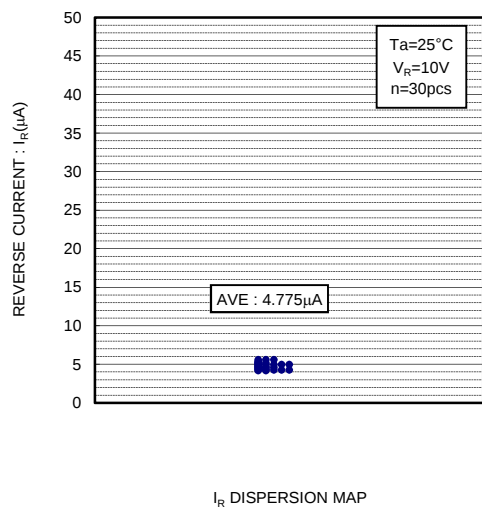
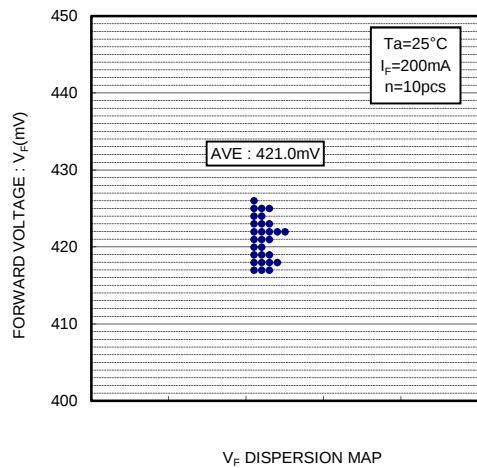
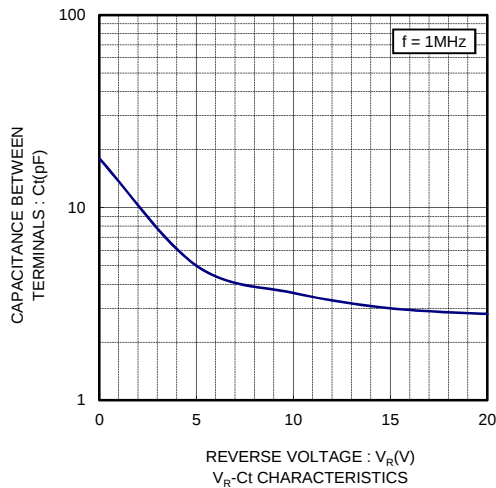
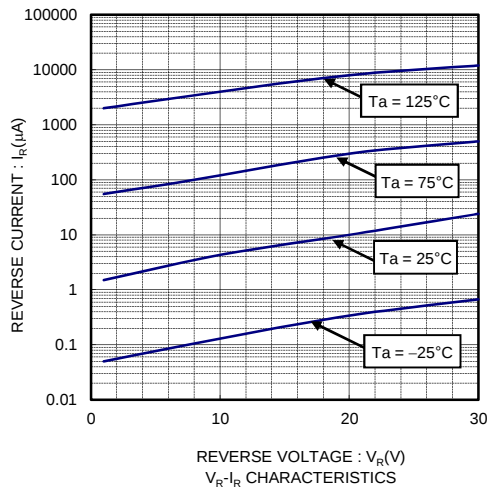
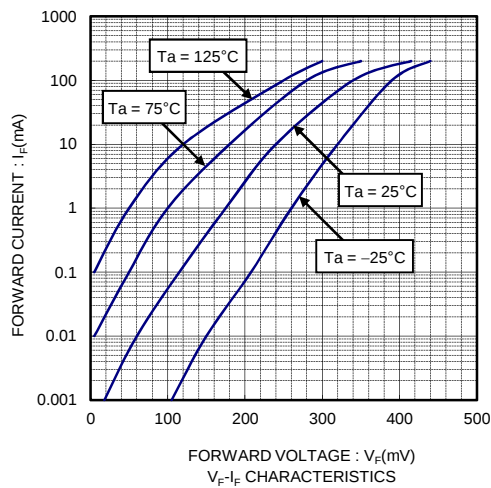
●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

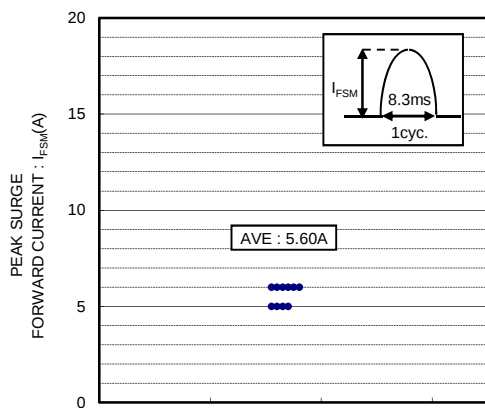
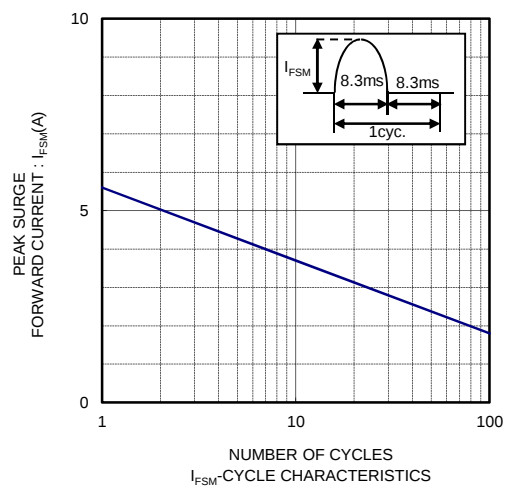
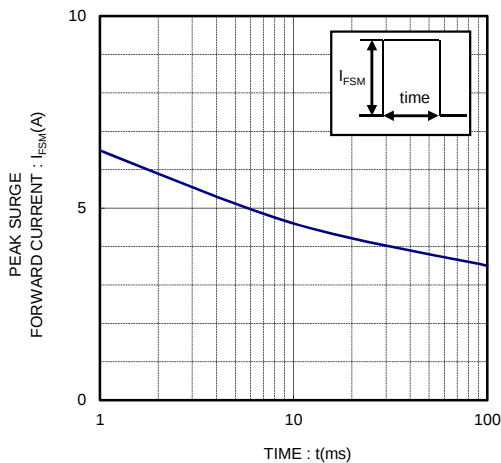
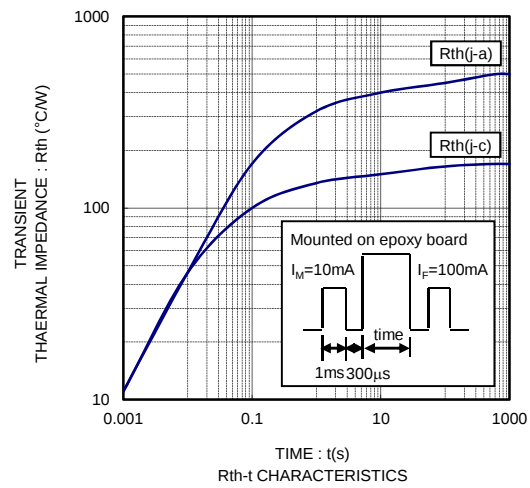
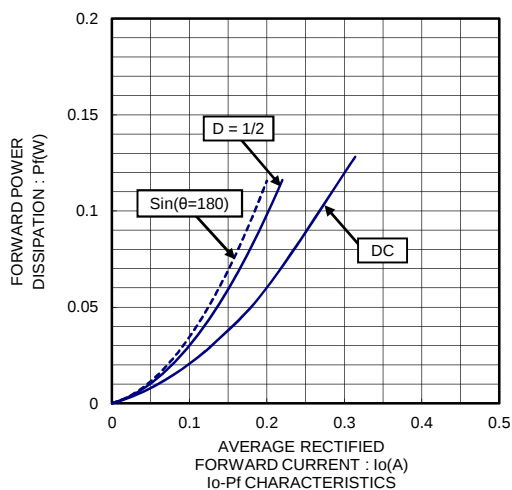
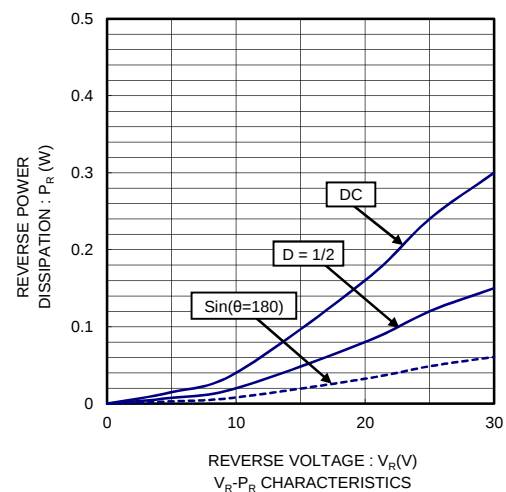
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	30	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current (*1)	I_o	200	mA
Forward current surge peak (60Hz·1cyc) (*1)	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

(*1) Rating of per diode

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	-	-	0.28	V	$I_F=10\text{mA}$
	V_{F2}	-	-	0.33	V	$I_F=100\text{mA}$
	V_{F3}	-	-	0.43	V	$I_F=100\text{mA}$
	V_{F4}	-	-	0.50	V	$I_F=100\text{mA}$
Reverse current	I_R	-	-	30	μA	$V_R=10\text{V}$



 I_{FSM} DISPERSION MAP I_{FSM} CYCLE CHARACTERISTICS I_{FSM} - t CHARACTERISTICS R_{th} - t CHARACTERISTICS I_O - P_F CHARACTERISTICS V_R - P_R CHARACTERISTICS

